NSN 5961-00-331-3234

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-331-3234 **Inclosure Material:** Metal **Overall Length:** 4.327 inches **Overall Diameter:** 1.443 inches **Mounting Facility Quantity: Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Overall Width Across Flats:** Between 1.218 inches and 1.250 inches **Thread Size:** 0.750 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 700.0 forward voltage, peak and 700.0 repetitive peak reverse voltage, peak total value, gate terminal open-circuited and 840.0 nonrepetitive peak reverse voltage, peak total value, gate terminal open-circuited **Current Rating Per Characteristic:** 3500.00 amperes source cutoff current peak **Power Rating Per Characteristic:** 10.0 watts small-signal input power, common-collector universal **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius ambient air **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 3 insulated wire lead w/terminal lug Shelf Life: N/a **Unit Of Measure:** Demilitarization: No Fiig: